

/ Revised record

F	2018-4				
G	2018-10-22				
H	2019-1-09	1			
I	2019-6-13		取消 RDSON@-20V/-10A 的项目		
J	2022-1-10		VGSS= $\pm 20V$ $\pm 25V$; IGSS VGSS= $\pm 20V$ $\pm 25V$ E		
A	2022-2-25	ALL	AOS-AOSP21307 BRCS4407SC		



SOP-8 P MOS

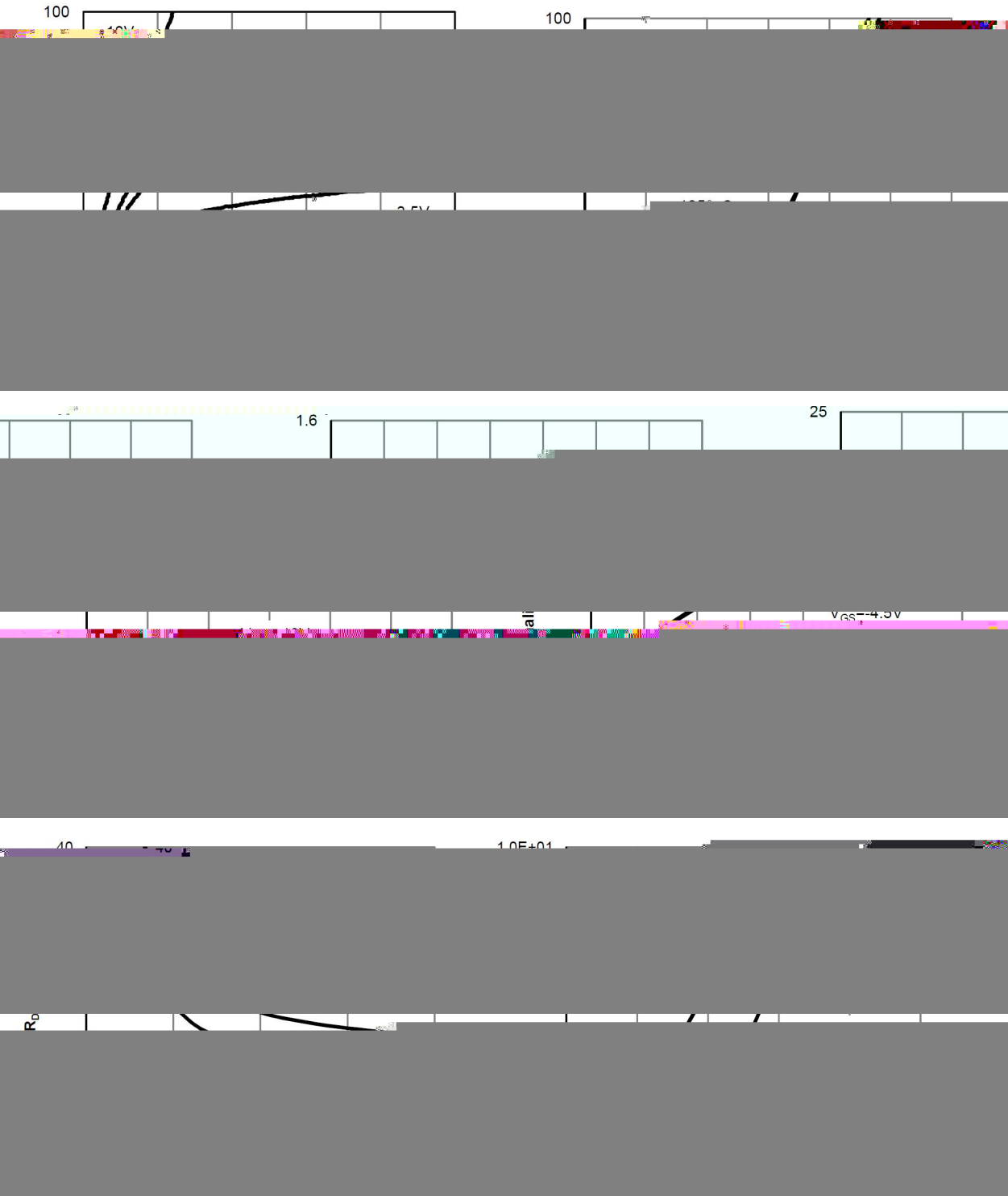
P-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

 $V_{DS} (V) = -30V$ $I_D = -14A (V_{GS} = \pm 25v$

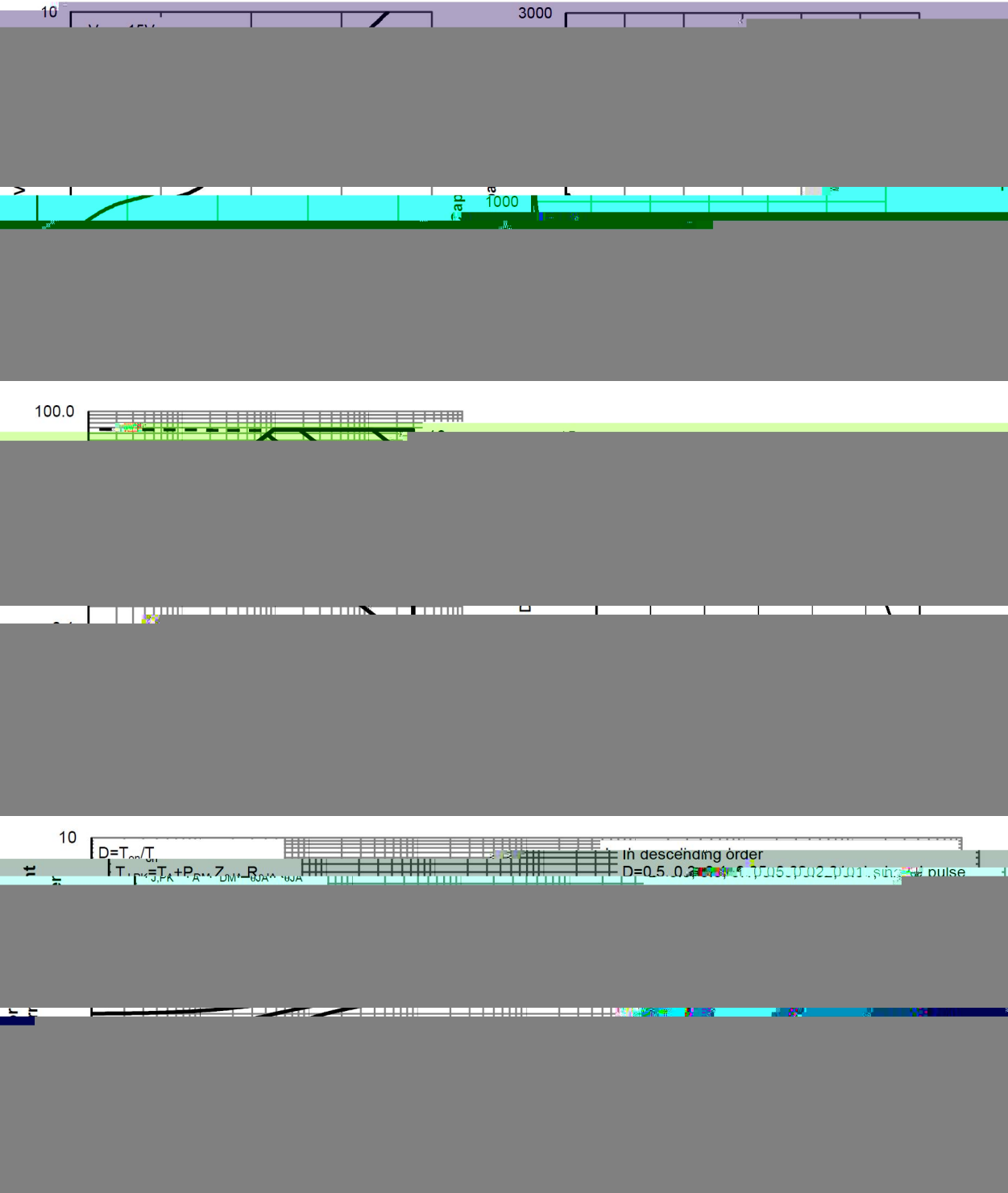
or n

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	± 25	V
Continuous Drain Current	$I_D (T_a=25^\circ\text{C})$	-14	A
Pulsed Drain Current	I_{DM}	-56	A
Power Dissipation for Single Operation	$P_D (T_a=25^\circ\text{C})$	3.1	W
Maximum Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	
Thermal Resistance-			

/ Electrical Characteristic Curve

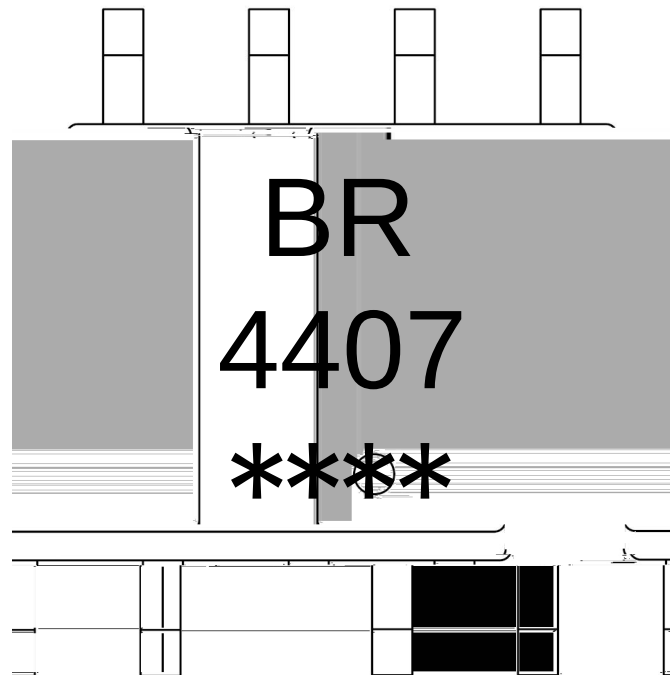


/ Electrical Characteristic Curve





/ Marking Instructions



BR

4407

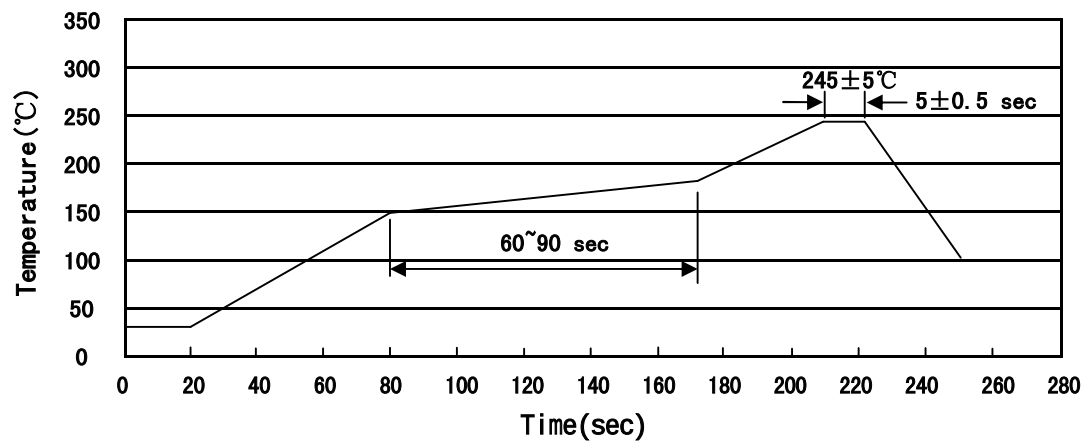
Note:

BR: Company Code

4407: Product Type

****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | |
|---|-------------|-----------|--|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180°C, Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5°C, Duration:5±0.5sec. |
| 3 | 2 10°C/sec. | | 3. Cooling Speed: 2~10°C/sec. |

/ Resistance to Soldering Heat Test Conditions

260±5°C 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
							盒	箱
						"		

/ Notices